

N-channel 120 V 6.7 mΩ standard level MOSFET in I2PAK 8 May 2013 Product data sheet

## 1. General description

Standard level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

### 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- I2PAK package for slimline adaptors & height constrained applications

## 3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control
- Slimline adaptors & chargers

## 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	120	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	-	70	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	405	W
Static chara	cteristics	·					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		4	5.7	6.7	mΩ
Dynamic cha	aracteristics	·			_		
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 60 V;		-	61.9	-	nC
Q <sub>G(tot)</sub>	total gate charge	<u>Fig. 14; Fig. 15</u>		-	207.1	-	nC
Avalanche r	uggedness	·					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{split} V_{GS} &= 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C};  \text{I}_{D} = 70 \text{ A}; \\ V_{sup} &\leq 120 \text{ V}; \text{ unclamped};  \text{R}_{GS} = 50  \Omega; \\ \hline \text{Fig. 3} \end{split}$		-	-	532	mJ

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G L F A
mb	D	drain	I2PAK (SOT226)	mbb076 S

## 6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PSMN6R3-120ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226					

## 7. Limiting values

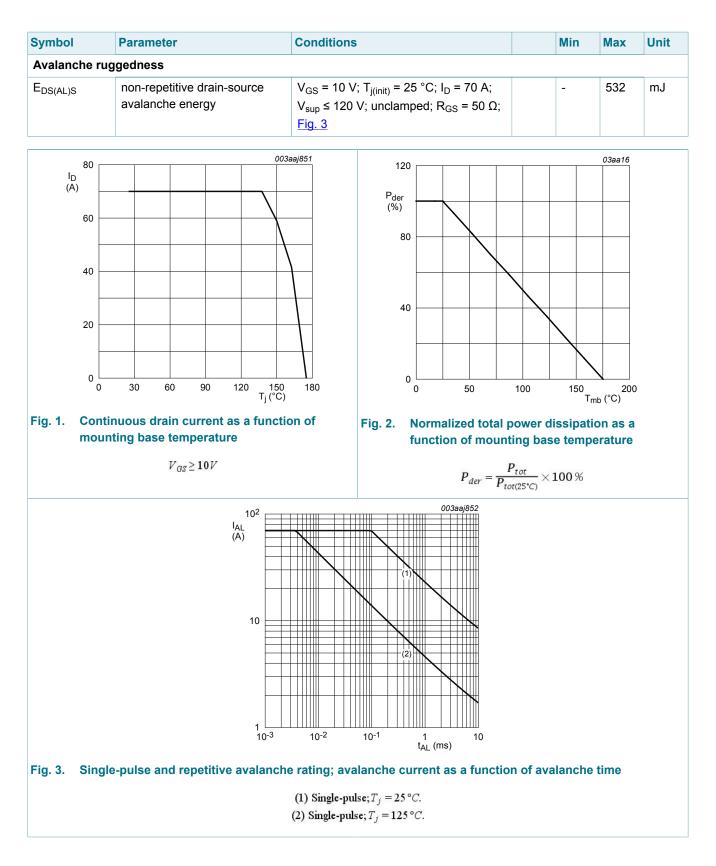
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	120	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	120	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	70	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	-	70	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 4	-	280	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	405	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-dra	in diode	· · ·			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	70	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	280	А

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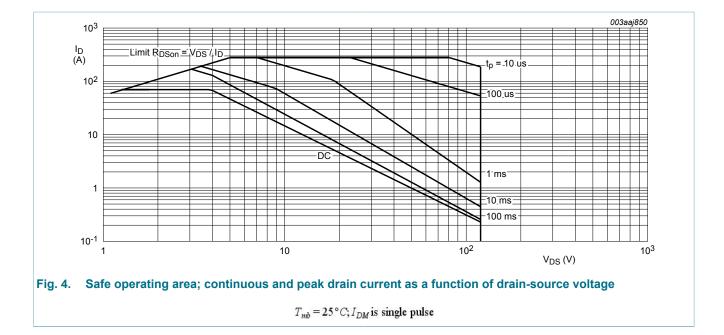
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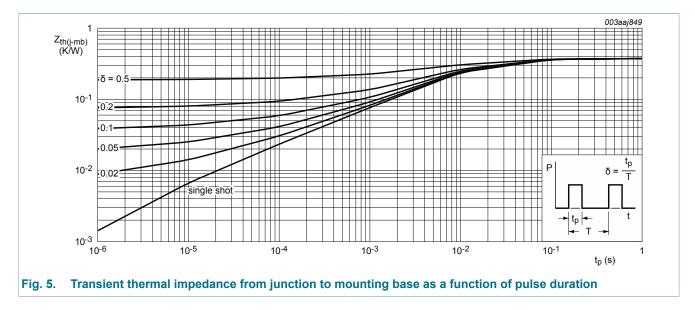
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## 8. Thermal characteristics

Table 5. Tl	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.3	0.37	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in free air	-	65	-	K/W



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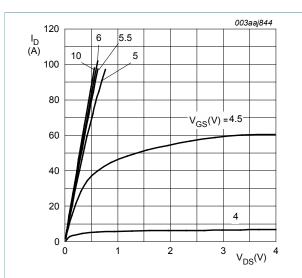
## 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	120	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	108	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10; Fig. 11	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 120 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.1	1	μA
		V <sub>DS</sub> = 120 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	4	5.7	6.7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 13; Fig. 12	-	16.5	19.4	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	0.44	0.88	1.76	Ω
Dynamic ch	aracteristics		1			
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 60 V; $V_{GS}$ = 10 V;	-	207.1	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 14; Fig. 15	-	43.2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	29.8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	13.4	-	nC
Q <sub>GD</sub>	gate-drain charge		-	61.9	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 60 V; <u>Fig. 14; Fig. 15</u>	-	4.3	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	11384	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	534	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	358	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 60 V; R <sub>L</sub> = 2.4 Ω; V <sub>GS</sub> = 10 V;	-	42.1	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	58.2	-	ns

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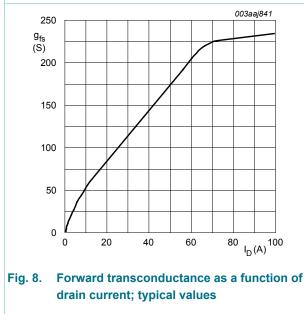
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
t <sub>d(off)</sub>	turn-off delay time			-	142.1	-	ns	
t <sub>f</sub>	fall time	_		-	67.7	-	ns	
Source-drain	Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>		-	0.79	1.2	V	
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 25 A; dI_{S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	76.1	-	ns	
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 60 V		-	264.2	-	nC	

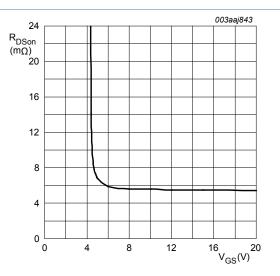




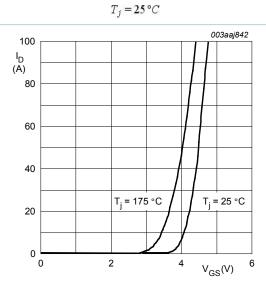




 $T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$ 





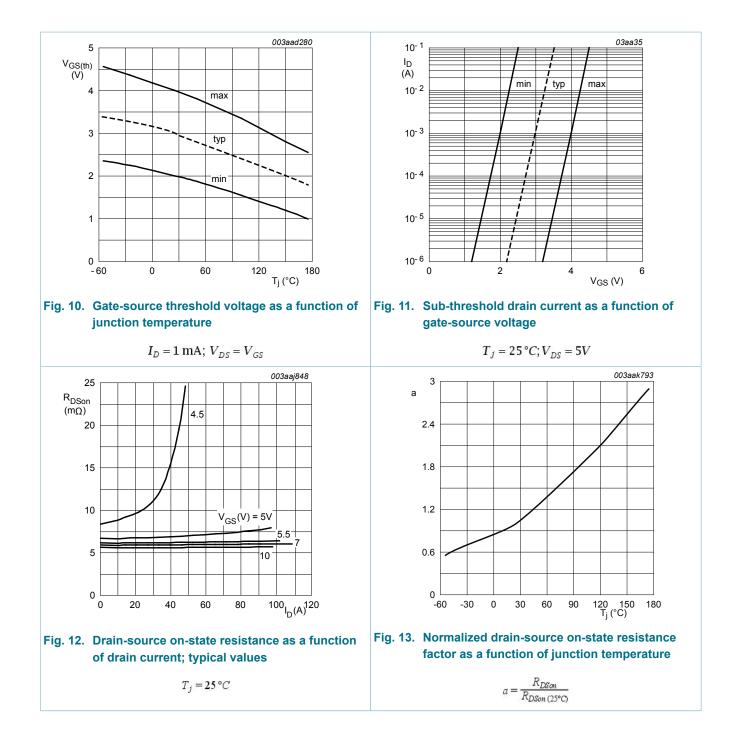




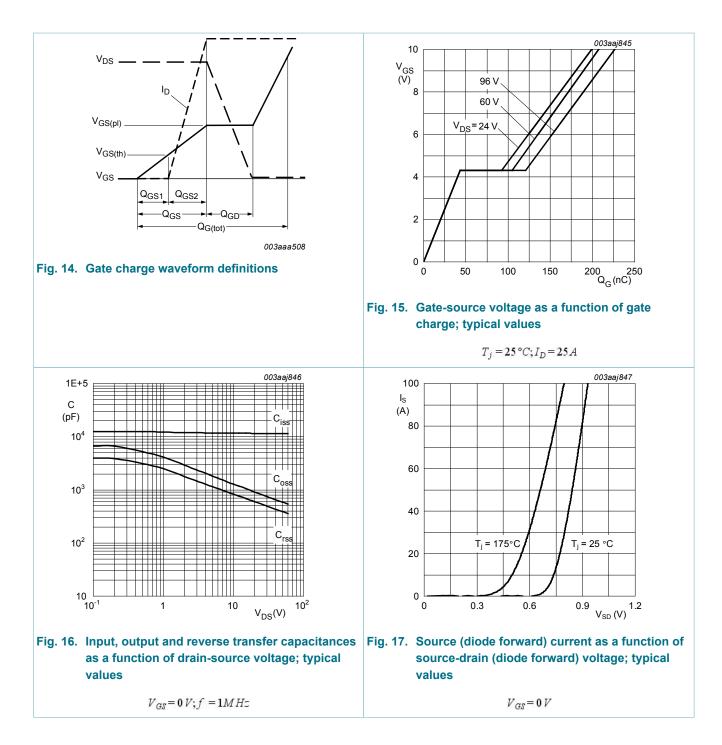
 $V_{DS} > I_D \times R_{DSon}$ 

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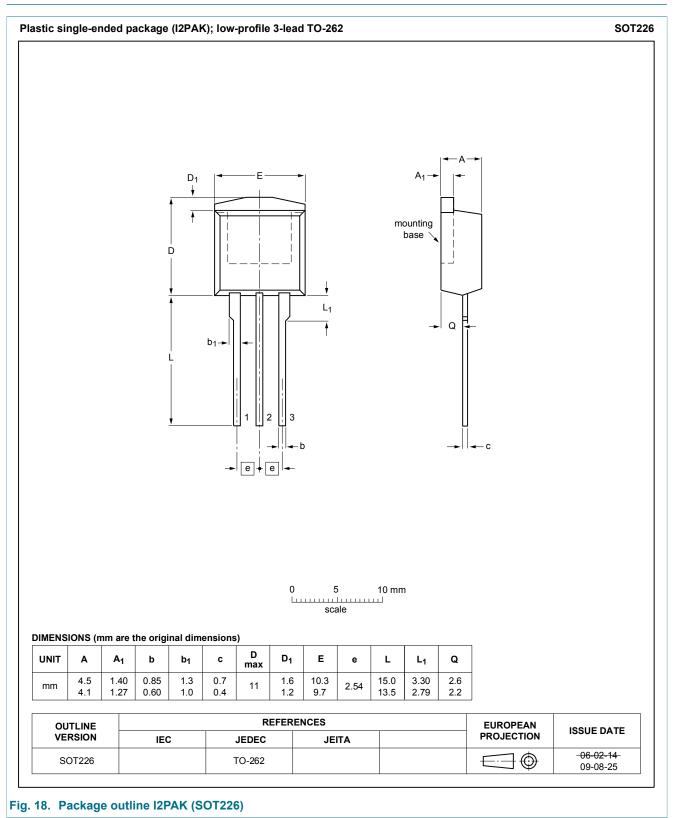


#### N-channel 120 V 6.7 m $\Omega$ standard level MOSFET in I2PAK



N-channel 120 V 6.7 m $\Omega$  standard level MOSFET in I2PAK

## 10. Package outline



#### N-channel 120 V 6.7 mΩ standard level MOSFET in I2PAK

#### 11. Legal information

#### 11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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